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Electronics, Magnetics and Photonics

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CONTENTS

- * **Creating Electrical Bistability Using Nano-bits – Application in 2-Terminal Memory Devices** 195
Iulia Salaoru, Sattam Alotaibi, Zahra Al Halafi,
and Shashi Paul
- * **SONOS Memories: Advances in Materials and Devices** 209
K. Ramkumar, V. Prabhakar, Ali Keshavarzi,
Igor Kouznetsov, and Sam Geha
- Electrical Study of Radiation Hard Designed HfO₂-based 1T-1R RRAM Devices** 223
Eduardo Pérez, Florian Tepy,
and Christian Wenger
- Experimental and Theoretical Studies of Resistive Switching in Grain Boundaries of Polycrystalline Transition Metal Oxide Film** 229
Takumi Moriyama, Sohta Hida,
Takahiro Yamasaki, Takahisa Ohno,
Satoru Kishida, and Kentaro Kinoshita
- Studies on Control of Oxygen Vacancies in MOD-made BaTiO₃ Thin Film by Nitrogen Annealing to Improve Resistive Switching Behavior for ReRAM Application** 235
S. Maejima, T. Sugie, K. Yamashita,
and M. Noda
- Magnetodielectric Coupling in Ferromagnetic/Ferroelectric/Ferromagnetic Spin Capacitor** 241
F. Aponte, R. Masso, K. Dasari,
G. Sreenivasulu, G. Srinivasan, and R. Palai
- Ion Beam Etch for Patterning of Resistive RAM (ReRAM) Devices . . .** 247
Narasimhan Srinivasan, Katrina Rook,
Ivan Berry, Binyamin Rubin, and Frank Cerio

*Invited Paper

**Structural and Magnetic Properties of Pure and Mn-Doped
Bismuth Ferrite Powders253**

Hector A. Chinchay Espino,
Gina M. Montes-Albino,
Christian O. Villa Santos,
and Oscar J. Perales Perez

**Enhanced Reliability of Top-pinned Perpendicular Magnetic
Tunnel Junction by Post-oxidation of Sputtered MgO Barrier259**

Chikako Yoshida, Hideyuki Noshiro,
Yuichi Yamazaki, and Toshihiro Sugii